

(use as many sheets as necessary)

Sheet	1	of	1
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Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu
Attorney Docket Number	2269-4218US (99-0796.00/US)

[illegible][illegible]

**Examiner
Signature**

HUNG VU

Date Considered

04/19/04

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				Application Number	09/651,620
				Filing Date	August 30, 2000
				First Named Inventor	Eugene P. Marsh
				Group Art Unit	2811
				Examiner Name	H. Vu
Sheet	1	of	2	Attorney Docket Number	2269-4218US (99-0796.00/US)

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
V _h		US-4,250,210	02/1981	Crosby et al.	
		US- 4,982,309	01/1991	Shepherd	
		US- 5,080,862	01/1992	Luthra	
		US- 5,128,016	06/1992	Glennings et al.	
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		US- 5,314,727	05/1994	McCormick et al.	
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		US- 5,994,034	11/1999	Maehata	
V _h		US- 6,197,628 B1	03/2001	Vaartstra et al.	

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Examiner Signature	HUNG VU	Date Considered	04/19/04
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STATEMENT BY APPLICANT**

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Sheet 2 of 2

Complete if Known

Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu
Attorney Docket Number	2269-42181 US (99-0796 00/1 US)

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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